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## ABSTRACT OF THE DISCLOSURE

Within a charged particle beam exposure method for forming a patterned resist layer there is employed separating at least one adjacent pair of fractured pattern elements employed in forming a contiguous latent pattern within a blanket resist layer a gap. By employing the gap, a patterned resist layer formed incident to development of the blanket resist layer is formed with enhanced pattern fidelity and enhanced critical dimension control.

PEST AVAILABLE COTY